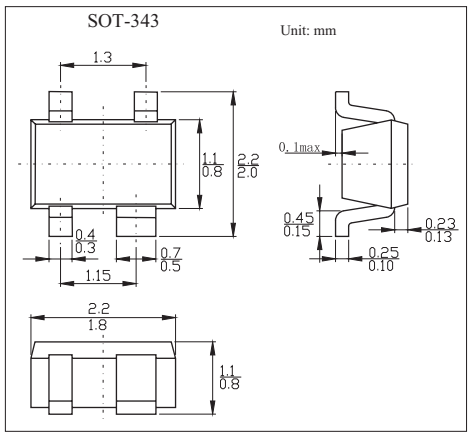
Silicon RF Switching Diode

BAR81W



Features

- Design for use in shunt configuration
- High shunt signal isolation
- Low shunt insertion loss

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Total power dissipation, T_S = 103℃	P_{tot}	100	mW
Junction temperature	T_j	150	℃
Operating temperature range	T_{op}	-55 to + 125	℃
Storage temperature range	T_{stg}	-55 to + 150	℃
Junction - ambient [1)]	$R_{th\ JA}$	≤ 200	K/W
Junction - soldering point	$R_{th\ JS}$	≤ 120	K/W

Note

1.Package mounted on alumina 15mm × 16.7mm × 0.7mm

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	I_R	V_R = 20 V			20	nA
Forward voltage	V_F	I_F = 100 mA		0.93	1	V
Diode capacitance	C_T	V_R = 1 V, f = 1 MHz		0.6		pF
		V_R = 3 V, f = 1 MHz		0.57		
Forward resistance	rf	I_F = 5 mA, f = 100 MHz		0.7		Ω
Series inductance	t_{rr}			0.15		nH

Marking

Marking	BBs